



# TOPOLOGICAL INSULATORS AND DIRAC SEMIMETALS — SYNTHESIS AND CHARACTERIZATION

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# OVERVIEW

- What are topological insulators and Dirac semimetals?
- Quantum transport and magnetic properties (quantum oscillations).
- Synthesis
- Some concrete materials and measurements.

# TOPOLOGICAL INSULATORS (TI)

## Topological insulator(TI)

Quantum state characterized by **topological invariant** (nontrivial).

There is an **energy gap**.

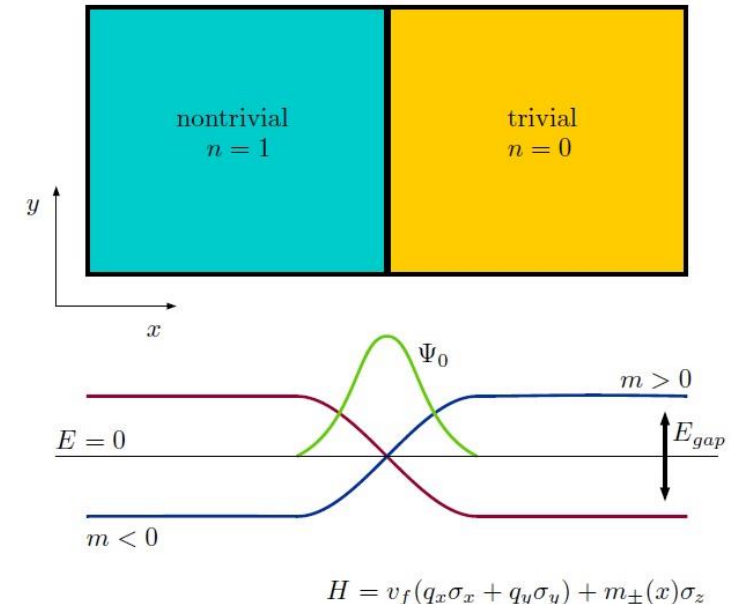
Defined over the wave functions (that give the energy gap)

⇒ Invariant under adiabatic change of Hamiltonian.

⇒ **The same as long as there is a gap!**

- Closing of the energy gap at the boundary of topological and normal insulator (vacuum)

⇒ **conductive edge/surface**

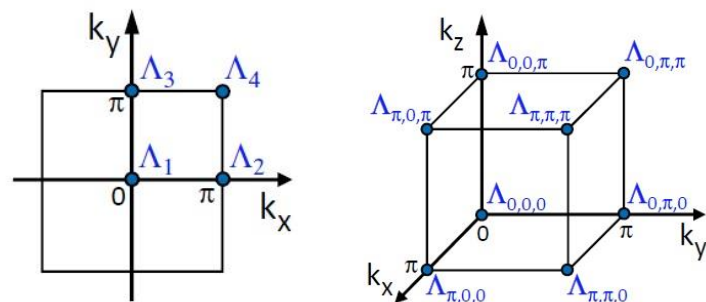


# TOPOLOGICAL INSULATORS

- Examples of TI and topological invariant ?

## $Z_2$ TI (TRS & IS)

Time reversal operator:  $\Theta^2 = -1$



$$2D: (-1)^\nu = \prod_{i=1}^4 \prod_{n=1}^N \xi_{2n}(\lambda_i)$$

parity

$\nu = 0, 1 \rightarrow Z_2$  topological invariant

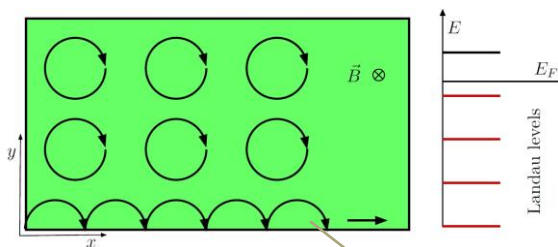
$$3D: \nu_0, \nu_1, \nu_2, \nu_3$$

## Topological crystalline insulator

$\nu = 0$ , topological invariant is not determined by TRS but with crystal symmetries (**mirror symmetry**).

$$M^2 = -1$$

## Quantum Hall effect

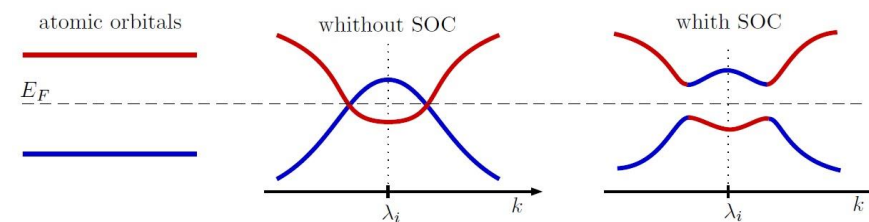


$$\sigma_{xy} = n \frac{e^2}{h}, \quad n \in \mathbb{N} \quad \text{Edge states}$$

$n \rightarrow$  topological invariant  
(Chern number or TKNN)

TRS, 2D

Nontrivial topological invariant if there is an **band inversion** at some  $\lambda$  !



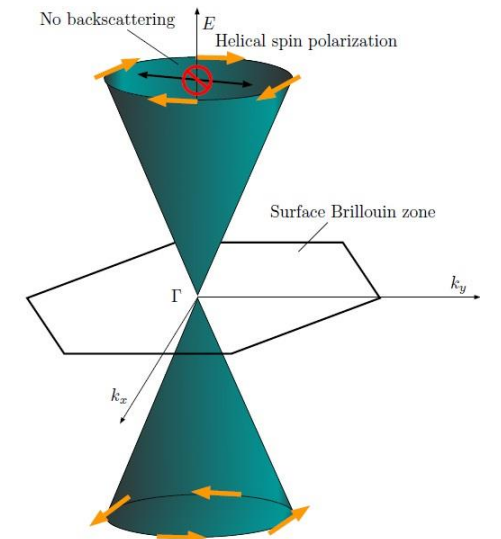
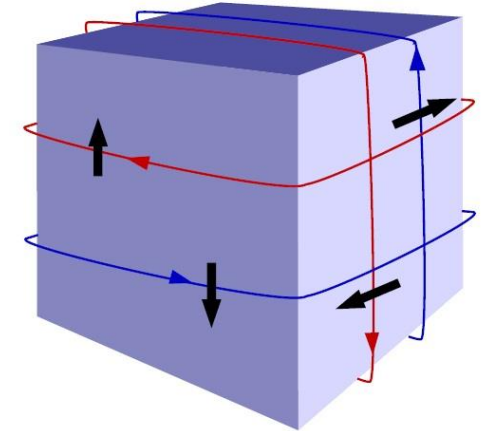
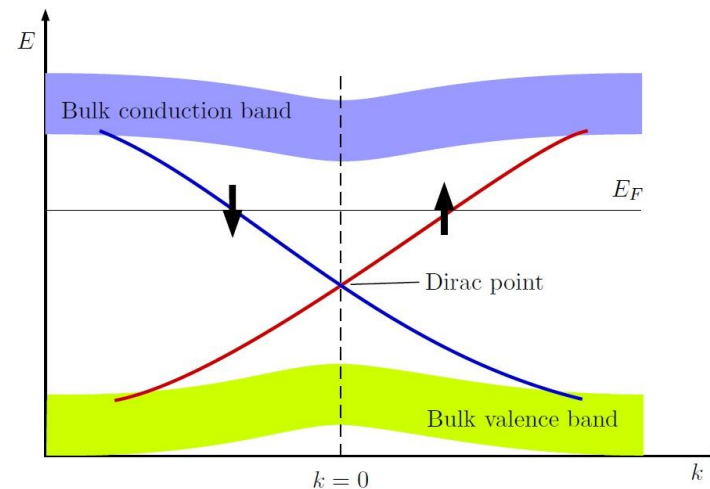
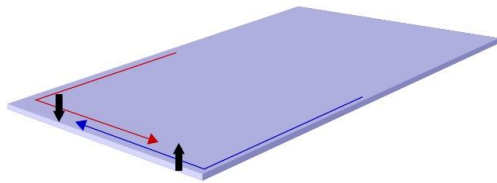
SOC – spin orbit coupling

# TOPOLOGICAL INSULATORS

- Edge/surface states properties.

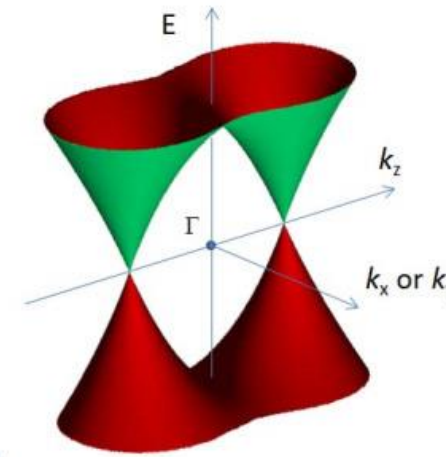
Dirac dispersion in low-energy excitations  $\longrightarrow$  high mobility!

Spin-momentum locking  $\longrightarrow$  forbidden backscattering!



# DIRAC SEMIMETALS

3D Dirac semimetal  $\text{Cd}_3\text{As}_2$



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027603 (2014)

## Dirac semimetal

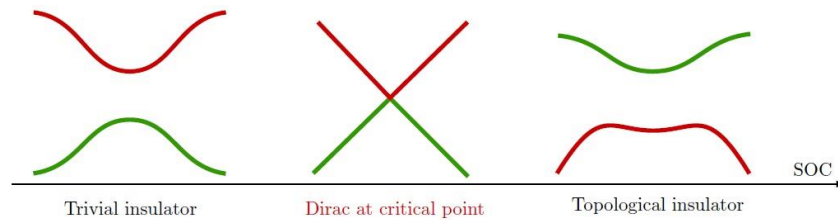
Dirac dispersion in  
the touch points.

Valence and conduction band touching in  
discrete points.

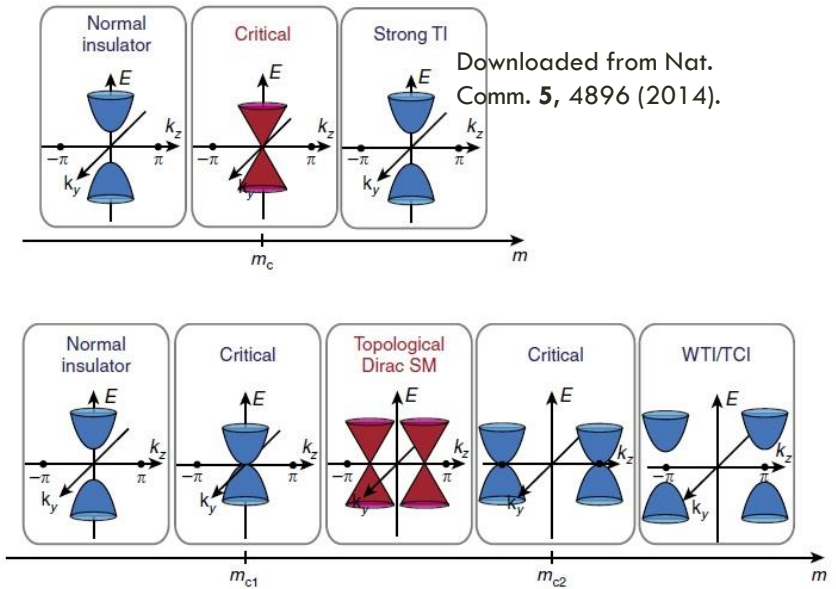
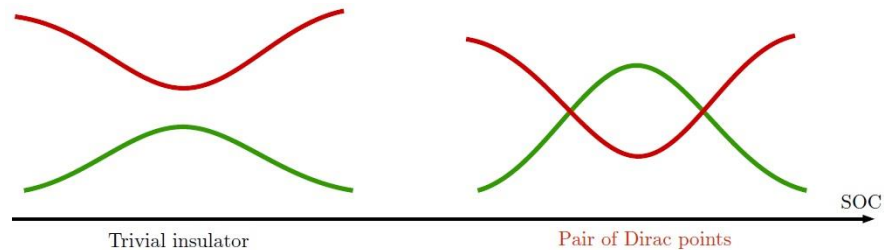
- **Dirac dispersion in 3D!**
- 2D – graphene:  $\hat{H}(\vec{k}) = v(k_x\sigma_x + k_y\sigma_y) \longrightarrow \text{SOC} \sim \sigma_z$  opens the gap.
- 3D:  $\hat{H}(\vec{k}) = v_{ij}k_i\sigma_j, \quad j = x, y, \textcircled{z} \longrightarrow \text{Robust against perturbations!}$

# DIRAC SEMIMETALS

- Dirac semimetals come in **two topological classes** too.
- Consequence of topological phase transition NI – TI.



- Intrinsic as a result of additional symmetries (rotational symmetry).



# TOPOLOGICAL INSULATORS & DIRAC SEMIMETALS

- Topological insulators  $\longrightarrow$  2D **Dirac** dispersion.
- Dirac semimetals  $\longrightarrow$  3D **Dirac** dispersion.

$\longrightarrow$  Possibility for investigating Dirac's fermion physics!

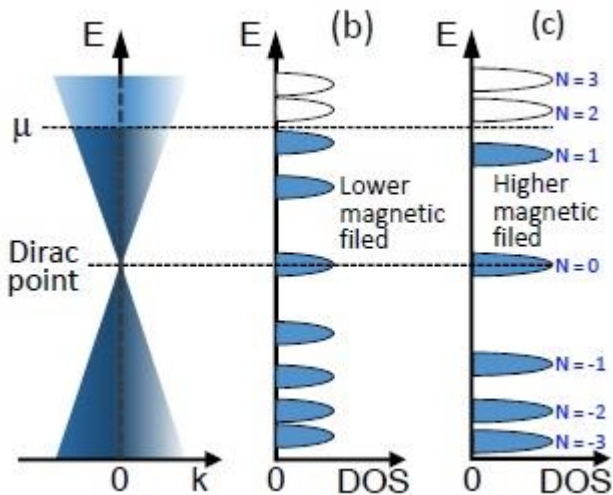
Evidence of Dirac fermions?



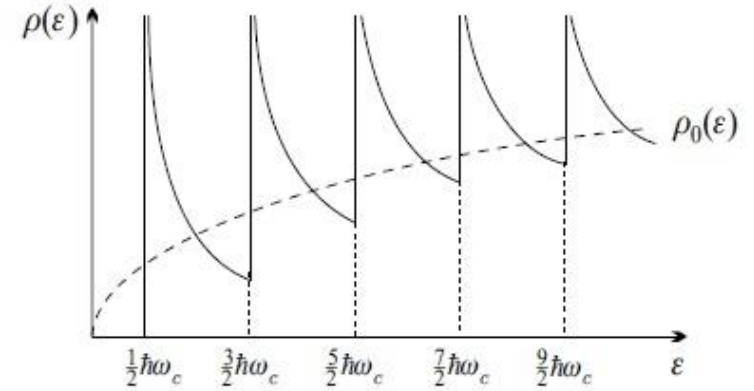
# QUANTUM OSCILLATIONS

- Electrons in strong B-field  $\longrightarrow$  Landau levels.

For Dirac dispersion  $E_{\pm}(k) = \pm v_f k$



$$E_{\pm}(N) = \pm \sqrt{(2e\hbar v_f^2 B / c) N}$$



$$E = \left( N + \frac{1}{2} \hbar \omega \right) + \frac{\hbar^2 k_z^2}{2m} \longrightarrow \text{for } E(k) = \frac{\hbar^2 k^2}{2m}$$

Periodic behavior of DOS.



Oscillations of physical quantities in  $1/B!$

$M \longrightarrow$  de Haas van Alphen oscillations.

$\sigma \longrightarrow$  Shubnikov de Haas oscillations.

# QUANTUM OSCILLATIONS

- de Haas van Alphen and Shubnikov de Haas oscillations (for 3D)

$$\Delta M = AR_T R_D R_s \sin \left[ 2\pi \left( \frac{F}{B} - \frac{1}{2} - \frac{1}{8} + \beta \right) \right]$$

$$\Delta \sigma_{xx} = AR_T R_D R_s \cos \left[ 2\pi \left( \frac{F}{B} - \frac{1}{2} - \frac{1}{8} + \beta \right) \right]$$

$2\pi\beta = \gamma$  Berry phase!

$$\gamma = i \oint_C d\vec{k} \langle \psi(\vec{k}) | \nabla_{\vec{k}} | \psi(\vec{k}) \rangle$$



For Dirac fermions

$$\gamma = \pi$$

$$R_T = \frac{\frac{\alpha T}{B}}{\sinh\left(\frac{\alpha T}{B}\right)}$$

$$R_D = e^{-\frac{\alpha T_D}{B}}$$

$$R_s = \cos\left(\frac{\pi}{2} g \frac{m}{m_0}\right)$$

Effective mass

$$\alpha = 14.69 \frac{m}{m_0} TK^{-1}$$

Informations about carrier density and Fermi surface shape.

$$F = \frac{\hbar}{2e} k_F^2$$

Quantum scattering time

$$T_D = \frac{\hbar}{2\pi k_B \tau}$$

# SYNTHESIS

- Aim: high quality monocrystal samples.
  - The fewer impurities and defects  $\longrightarrow$  minimize the influence of bulk states and increase mobility.



Sealing the quartz tube.



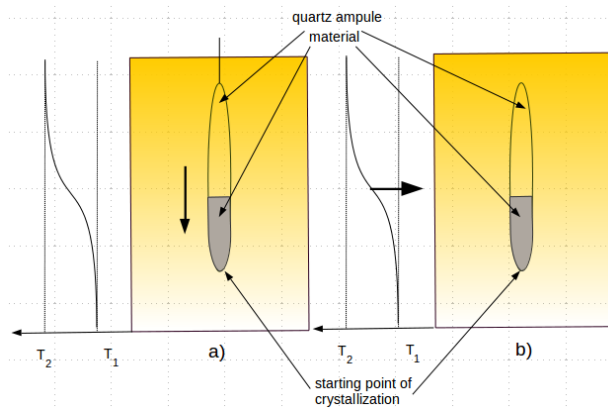
Material in vacuum sealed quartz ampoule (vacuum  $\sim 10^{-6}$  mbar)

High vacuum in ampoule

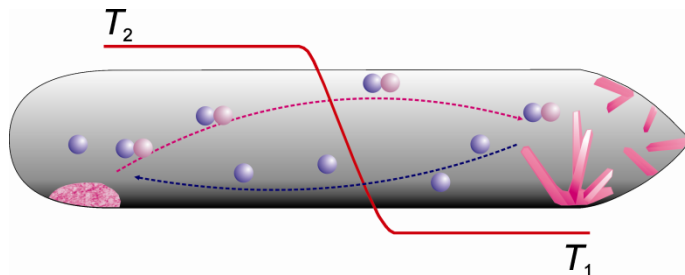
- clean atmosphere
- volatile elements

# SYNTHESIS

- Modified Bridgman method.



- (Chemical) vapor deposition.



Temperature gradient is achieved by two-zone tube furnaces.

Synthesis parameters:  
temperature, gradient, heating/cooling rate, growth time,  
amount and shape of material, ampoule dimensions.

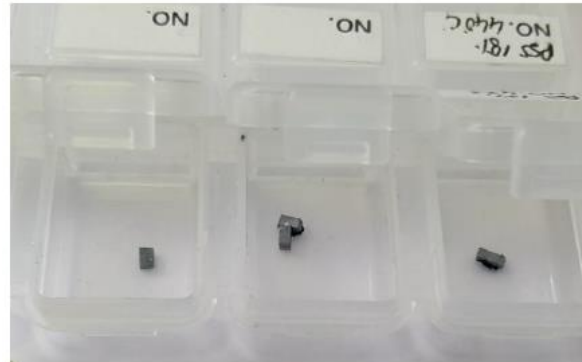
**Optimization of parameters!**

# SYNTHESIS

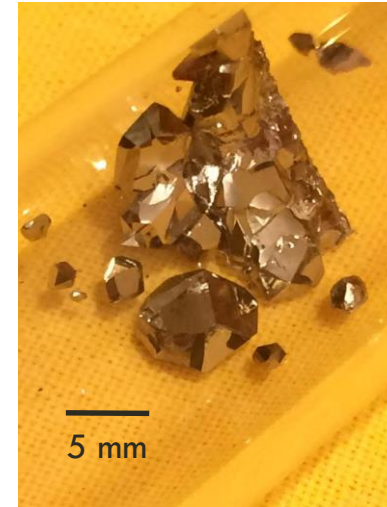
- Results of synthesis:



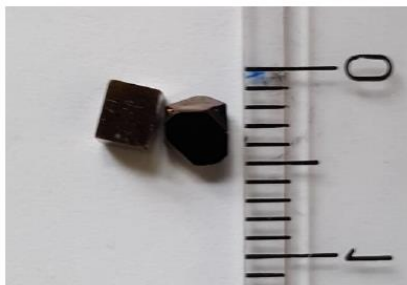
BiSbTeSe<sub>2</sub>



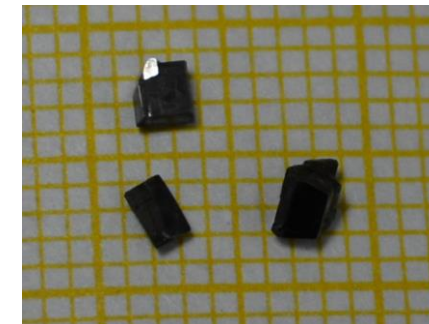
PbSnSe



Cd<sub>3</sub>As<sub>2</sub>



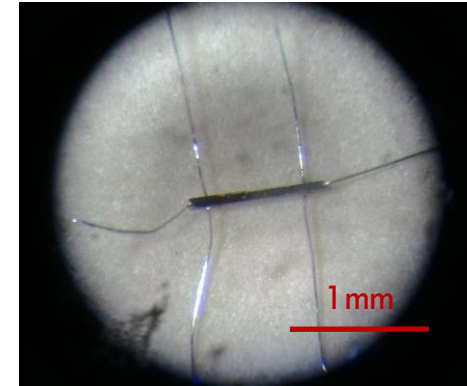
SnTe



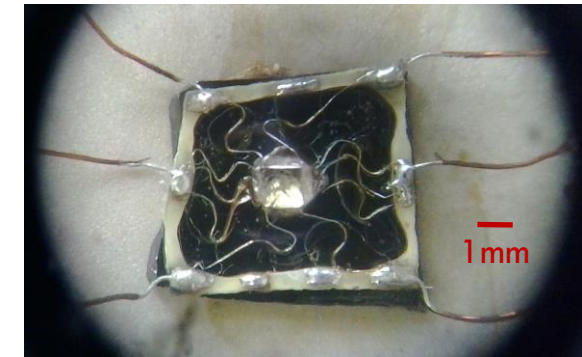
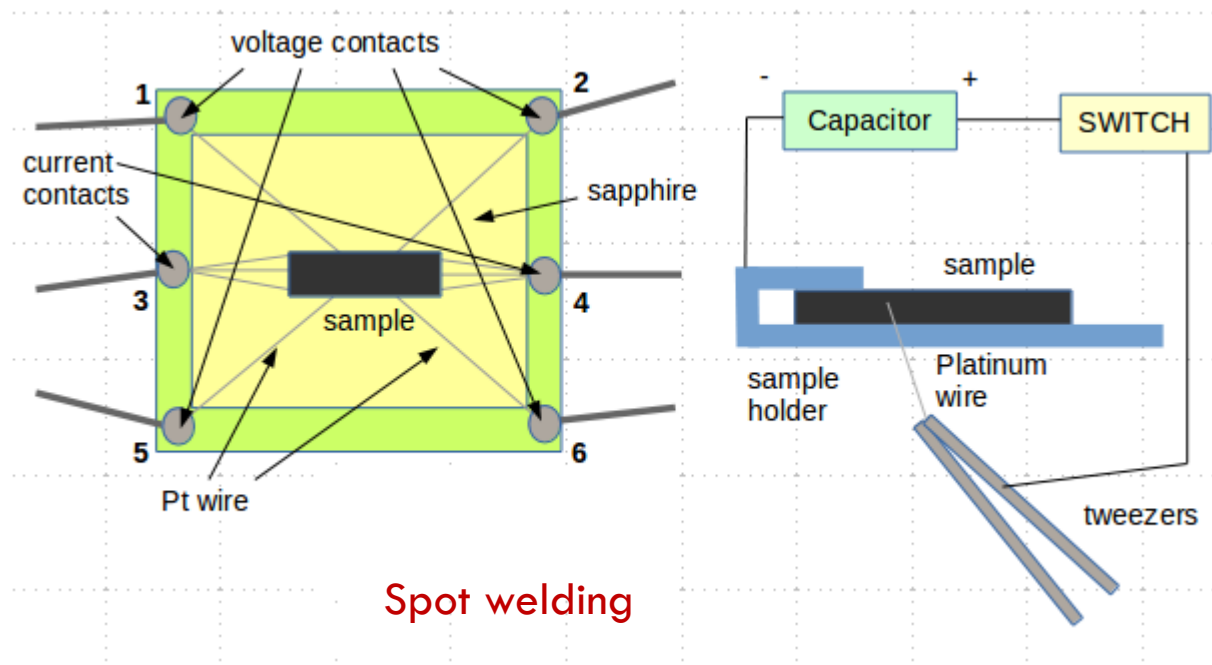
TaP

# SAMPLE PREPARATION

- For transport measurements good contacts are crucial ( $\sim \Omega$ ).

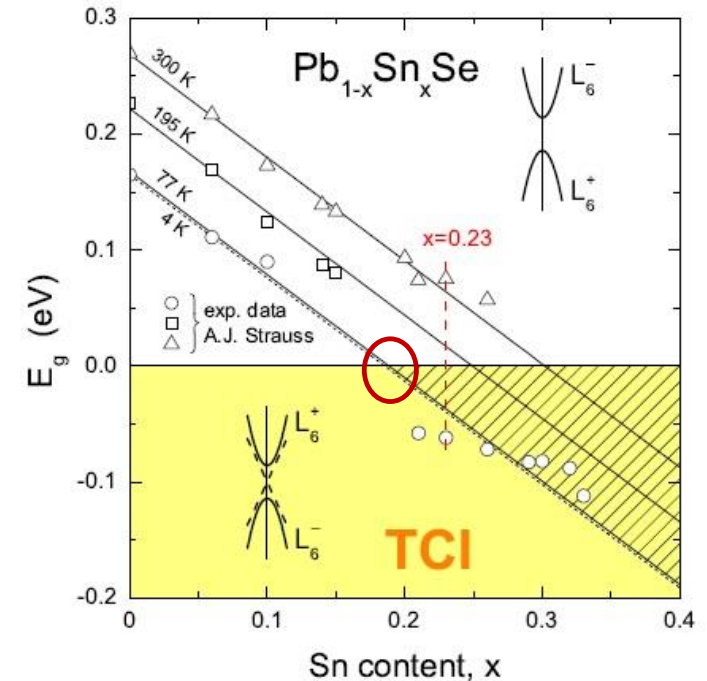


Samples of Cd<sub>3</sub>As<sub>2</sub> with contacts.



# PbSnSe

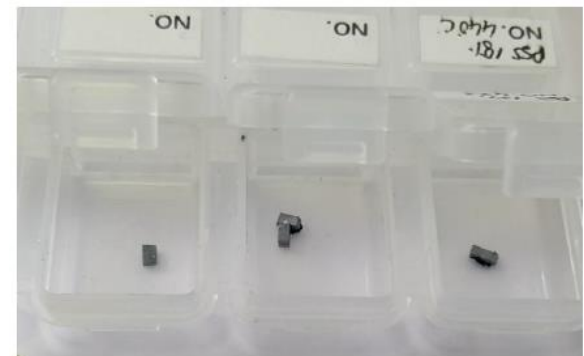
- $\text{Pb}_{1-x}\text{Sn}_x\text{Se}$  is a **topological crystalline insulator** for  $x > 0.23$ .
- Known for ages  $\longrightarrow$  energy gap depends on the T and x.  
 $\longrightarrow$  Topological phase transition with T or x.



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608-611 (1967)

- What happens at the transition point? ( $x \approx 0.18$ )

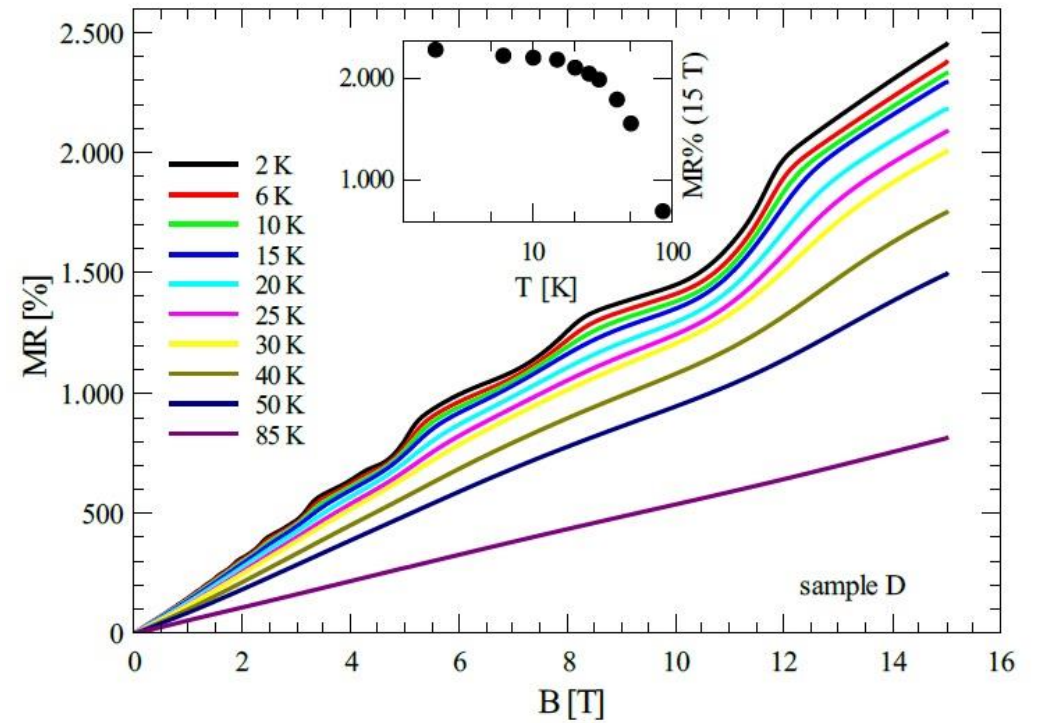
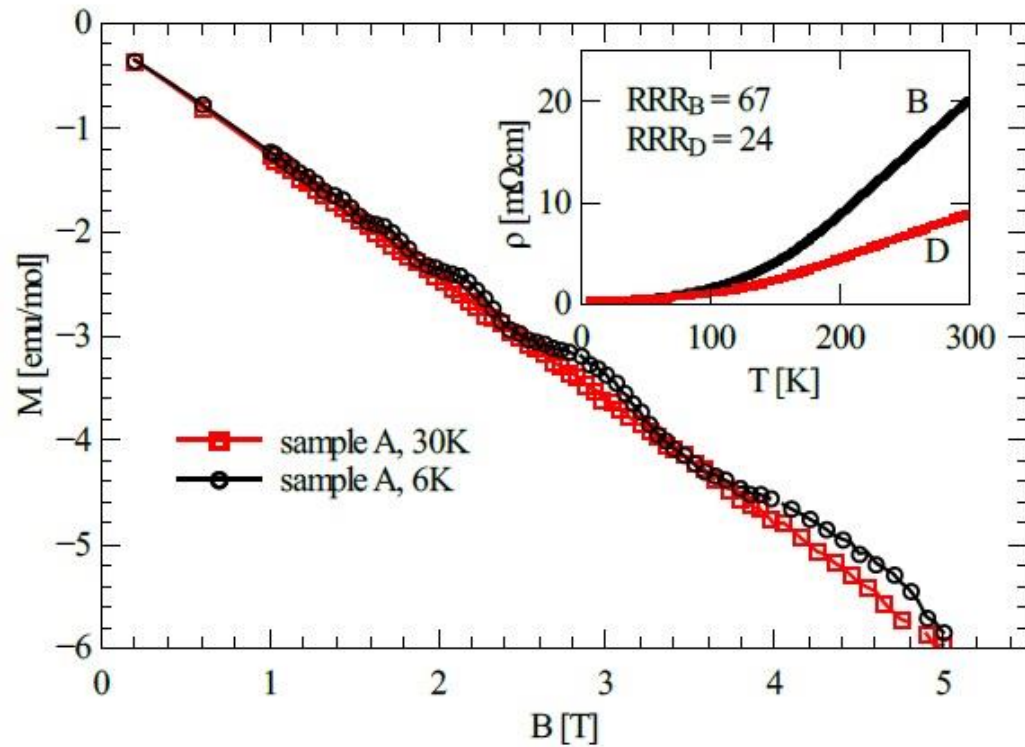
$x = 0.17, 0.18$





# PbSnSe

- Magnetization (**SQUID**) and magnetoresistance measurements in  $\text{Pb}_{0.82}\text{Sn}_{0.18}\text{Se}$ .

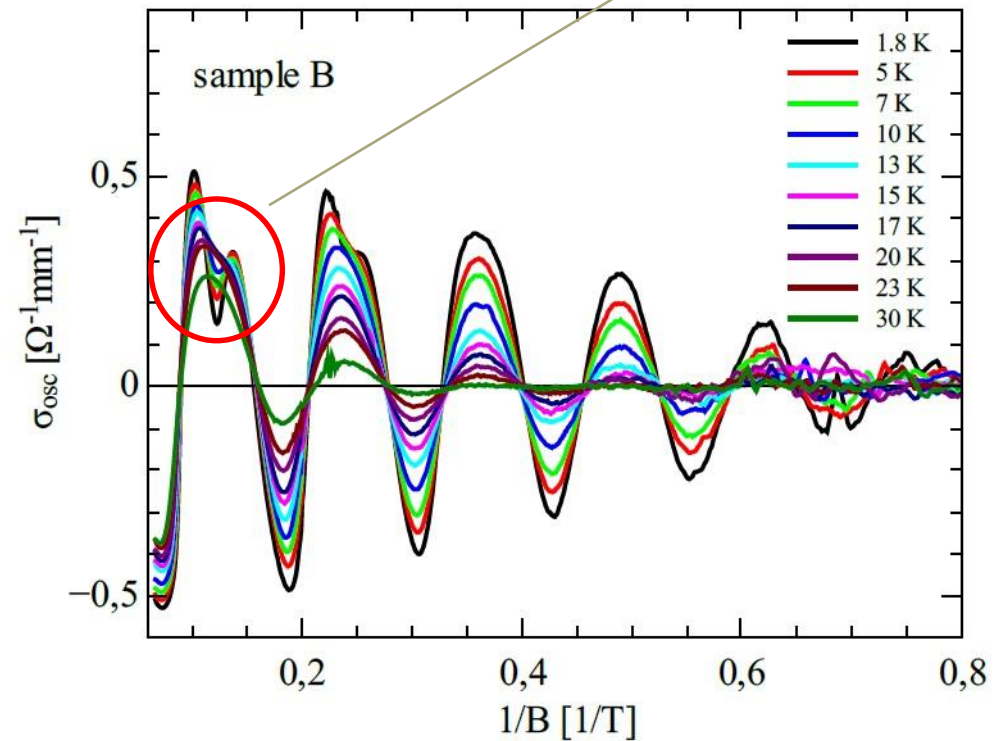
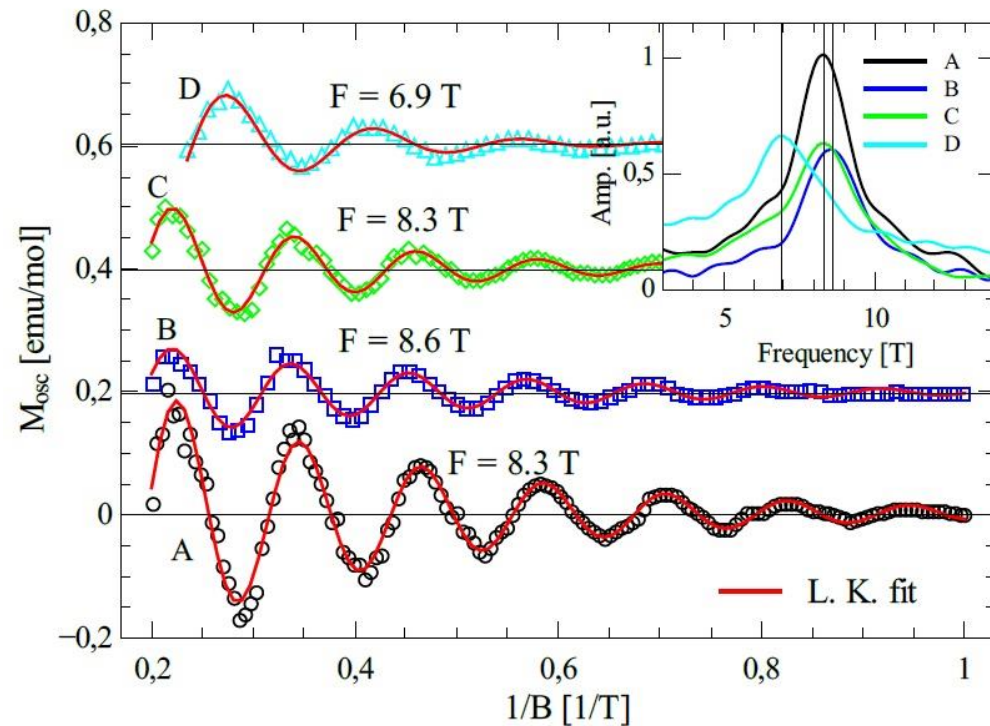




# PbSnSe

- By subtracting the background we get a pure oscillatory part.

Zeeman splitting of Landau levels.



# PbSnSe

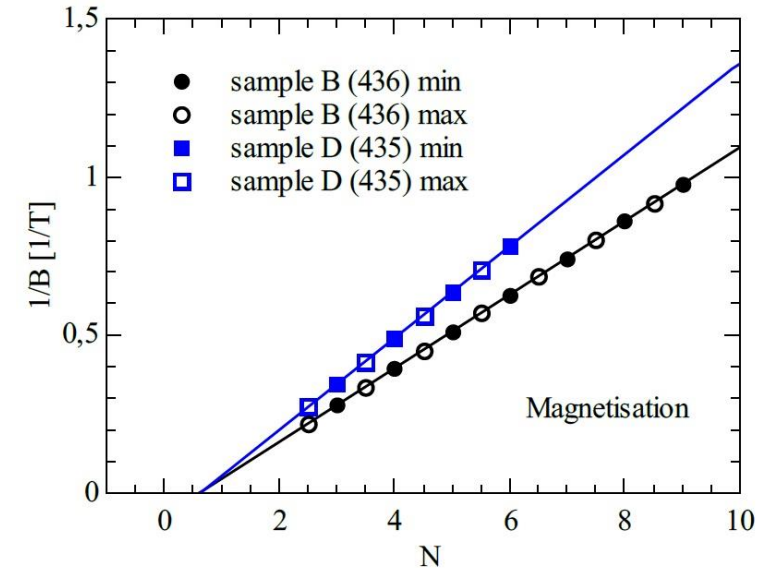
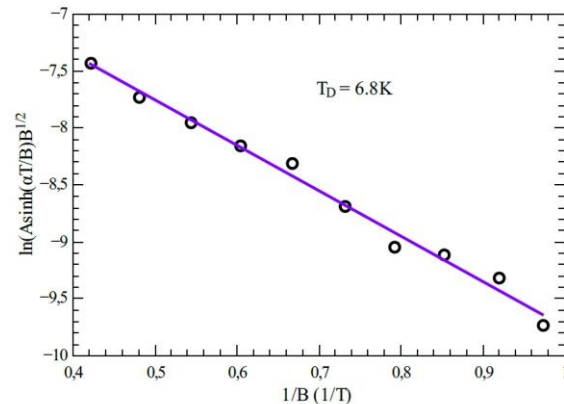
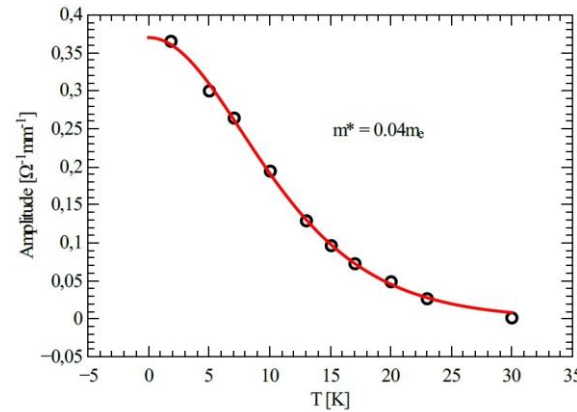
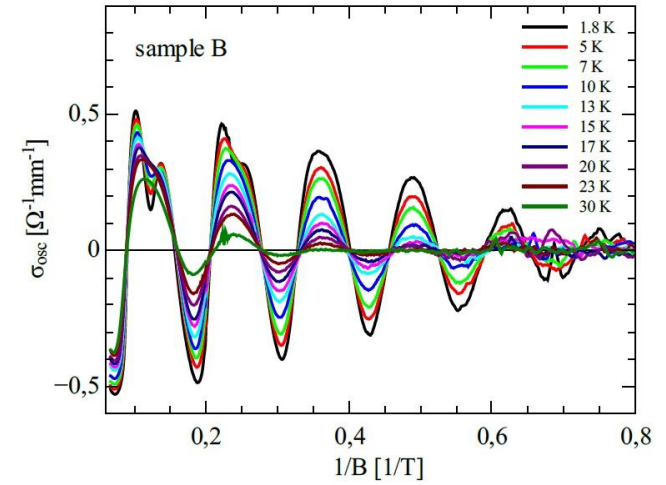
- How to get physical values from quantum oscillations?

$$\Delta M = AR_T R_D R_s \sin \left[ 2\pi \left( \frac{F}{B} - \frac{1}{2} - \frac{1}{8} + \beta \right) \right]$$

$$\Delta \sigma_{xx} = AR_T R_D R_s \cos \left[ 2\pi \left( \frac{F}{B} - \frac{1}{2} - \frac{1}{8} + \beta \right) \right]$$

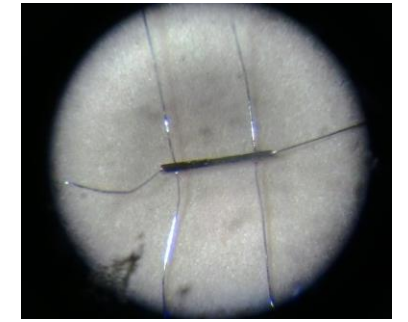
$$R_T = \frac{\frac{\alpha T}{B}}{\sinh \left( \frac{\alpha T}{B} \right)}$$

$$R_D = e^{-\frac{\alpha T_D}{B}}$$

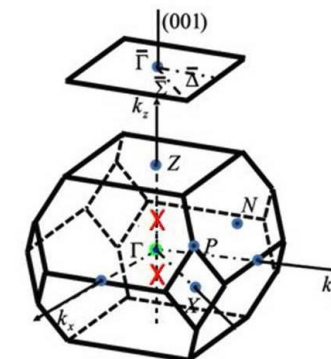
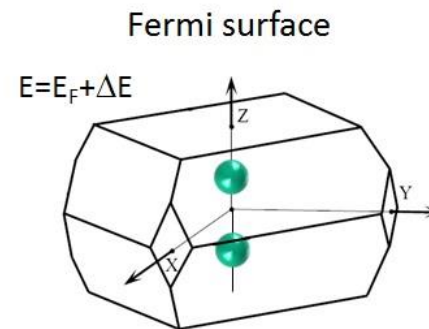


$$2\pi \left( \frac{F}{B} - \frac{1}{2} - \frac{1}{8} + \beta \right) = \pi \left( 2N - \frac{1}{2} \right)$$

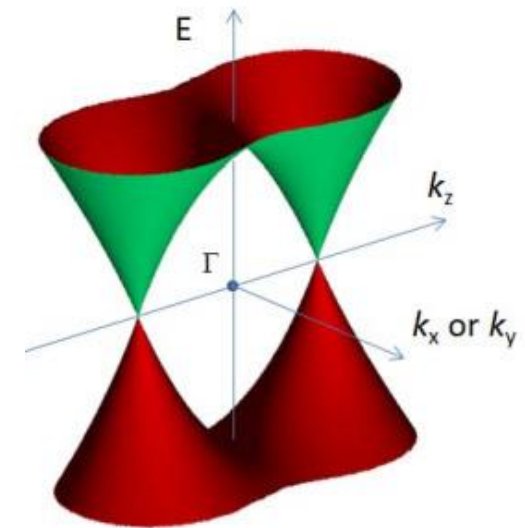
# Cd<sub>3</sub>As<sub>2</sub>



- Cd<sub>3</sub>As<sub>2</sub> is an intrinsic (nontrivial) Dirac semimetal.
- Very stable material, except toxicity ideal for application and experiment.
- High mobility  $\sim 10^6 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ .
- A pair of Dirac points in the direction of rotational symmetry axis ( $k_z$ ).
- Anisotropy of Fermi surface?  $\longrightarrow$  Different frequencies for different direction of magnetic field.



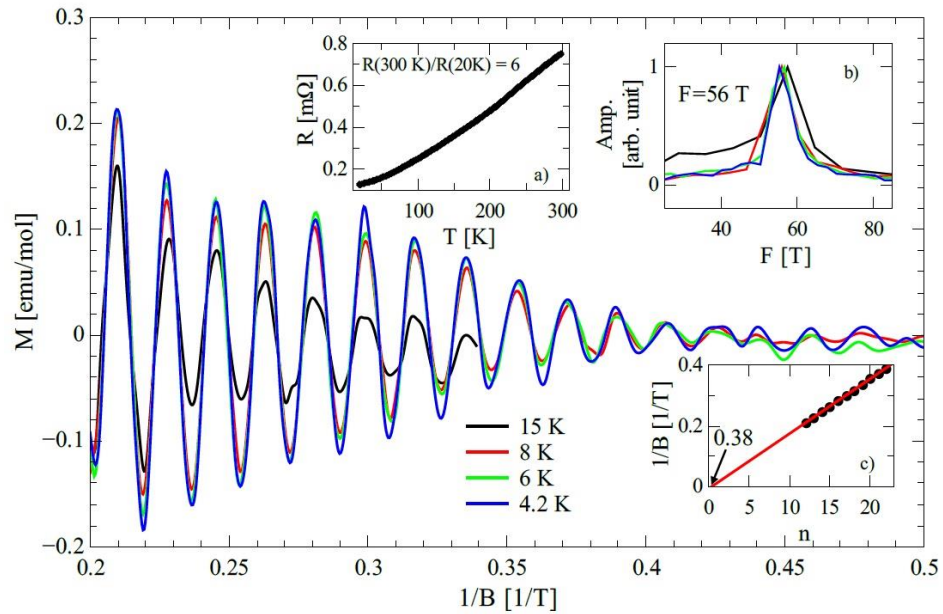
3D Dirac semimetal Cd<sub>3</sub>As<sub>2</sub>



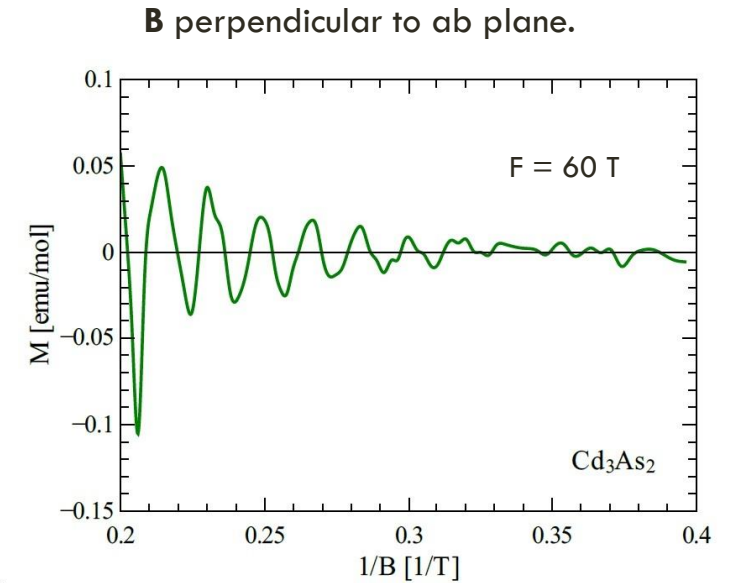
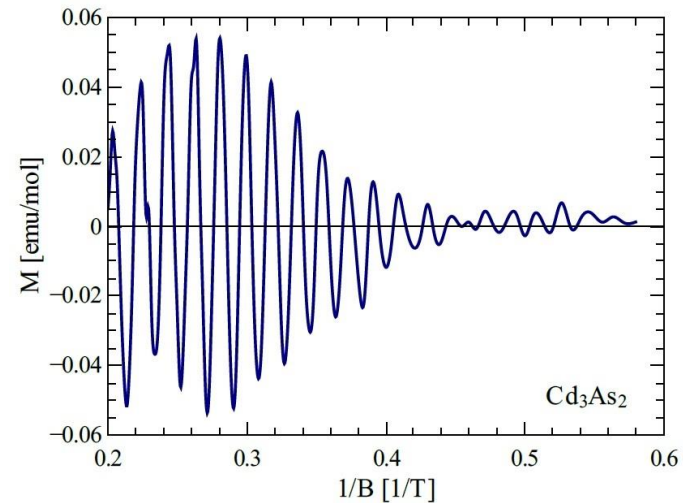
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# Cd<sub>3</sub>As<sub>2</sub>

- Magnetization and magnetoresistance are measured.



**B** in ab plane.

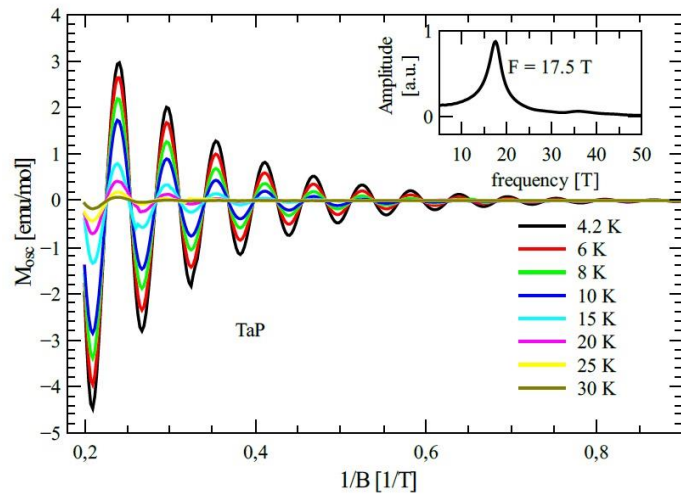


→ Superposition of frequencies.

# OTHER MATERIALS

- Other materials we have successfully synthesized:

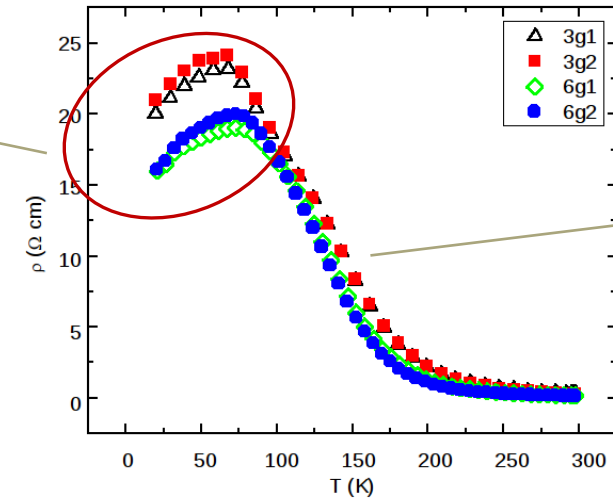
**TaP** → **Weyl semimetal** candidate.



Successfully observed quantum oscillations.


**BiSbTe<sub>2</sub>S** → topological insulator.

Metallic behavior  
because off surface  
states.



Typical semiconducting  
behavior

# CONCLUSION

- Topological insulators.
  - symmetry protected surface states  $\longrightarrow$  spin locking and robustness at nonmagnetic impurities.
-  An insight into the physics of Dirac 's fermions.
- Dirac semimetals.
  - 3D analogue of graphene. Symmetry protected Dirac points.
- The idea is to synthesize (**determination of synthesis parameters**) and characterize the obtained materials.
- Examine the consequences of the Dirac nature of carriers in **magnetization and transport**.